



#### 30V N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

| BV <sub>DSS</sub> | R <sub>DS(ON)</sub> max        | I <sub>D</sub> max<br>T <sub>A</sub> = +25°C |
|-------------------|--------------------------------|--|
|                   | 20.5mΩ @ V <sub>GS</sub> = 10V | 8.3A   |
| 30V               | 30mΩ @ V <sub>GS</sub> = 4.5V  | 7.4A   |

### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

### **Features and Benefits**

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm<sup>2</sup>
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
   A listing can be found at

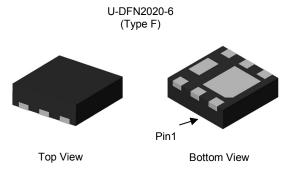
https://www.diodes.com/products/automotive/automotive-products/.

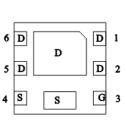
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

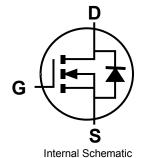
https://www.diodes.com/quality/product-definitions/

### **Mechanical Data**

- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.0065 grams (Approximate)







Pinout Bottom View

Ordering Information (Note 4)

| Part Number    | Case                 | Packaging          |
|----------------|----------------------|--------------------|
| DMN3025LFDF-7  | U-DFN2020-6 (Type F) | 3000/Tape & Reel   |
| DMN3025LFDF-13 | U-DFN2020-6 (Type F) | 10,000/Tape & Reel |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.



### **Marking Information**

Site1



S6 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)M = Month (ex: 9 = September)

Date Code Key

| Date Code Ney |      |     |     |      |      |     |     |      |      |     |     |      |
|---------------|------|-----|-----|------|------|-----|-----|------|------|-----|-----|------|
| Year          | 2017 | 20  | 18  | 2019 | 2020 | 20  | )21 | 2022 | 2023 | 20  | 24  | 2025 |
| Code          | Е    |     | F   | G    | Н    |     | I   | J    | K    |     | L   | М    |
| Month         | Jan  | Feb | Mar | Apr  | May  | Jun | Jul | Aug  | Sep  | Oct | Nov | Dec  |
| Code          | 1    | 2   | 3   | 4    | 5    | 6   | 7   | 8    | 9    | 0   | N   | D    |

Site 2



S6 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020)W = Week (ex: a = week 27; z represents week 52 and 53)
X = Internal code (ex: U = Monday)

Date Code Kev

| Date Code Ite |      |      |      |      |      |      |      |      |
|---------------|------|------|------|------|------|------|------|------|
| Year          | 2019 | 2020 | 2021 | 2022 | 2023 | 2024 | 2025 | 2026 |
| Code          | 9    | 0    | 1    | 2    | 3    | 4    | 5    | 6    |

| Week | 1-26 | 27-52 | 53 |
|------|------|-------|----|
| Code | A-Z  | a-z   | z  |

| Internal Code | Sun | Mon | Tue | Wed | Thu | Fri | Sat |
|---------------|-----|-----|-----|-----|-----|-----|-----|
| Code          | T   | U   | V   | W   | X   | Υ   | Z   |



## **Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

| Characteristic  |                 | Symbol                                       | Value            | Units      |    |
|---|-----------------|--|------------------|------------|----|
| Drain-Source Voltage                                    |                 |  | $V_{DSS}$        | 30         | V  |
| Gate-Source Voltage                                     |                 |  | V <sub>GSS</sub> | ±20        | V  |
| Continuous Drain Current (Note 6) \ = 40\               | Steady<br>State | $T_A = +25^{\circ}C$<br>$T_A = +70^{\circ}C$ | I <sub>D</sub>   | 8.3<br>6.6 | А  |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V | t < 10s         | $T_A = +25^{\circ}C$<br>$T_A = +70^{\circ}C$ | I <sub>D</sub>   | 9.9<br>7.9 | А  |
| Maximum Continuous Body Diode Forward Curre             | nt (Note 6)     |  | I <sub>S</sub>   | 3          | Α  |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1        | I <sub>DM</sub> | 40   | Α                |            |    |
| Avalanche Current (L = 0.1mH) (Note 7)                  | I <sub>AS</sub> | 15   | Α                |            |    |
| Avalanche Energy (L = 0.1mH) (Note 7)                   |                 |  | E <sub>AS</sub>  | 11         | mJ |

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                                   |                        | Symbol                           | Value       | Units |  |
|--|------------------------|----------------------------------|-------------|-------|--|
| Total Dawer Dissination (Note 5)                 | T <sub>A</sub> = +25°C |                                  | 0.66        | W     |  |
| Total Power Dissipation (Note 5)                 | $T_A = +70^{\circ}C$   | $P_{D}$                          | 0.42        | VV    |  |
| Thormal Desigtance Junction to Ambient (Note 5)  | Steady State           | П                                | 173         | °C/W  |  |
| Thermal Resistance, Junction to Ambient (Note 5) | t < 10s                | $R_{\theta JA}$                  | 133         | C/VV  |  |
| Total Power Dissipation (Note 6)                 | T <sub>A</sub> = +25°C | Б                                | 2.1         | W     |  |
| Total Power Dissipation (Note 6)                 | $T_A = +70^{\circ}C$   | $P_{D}$                          | 1.3         | ۷V    |  |
| Thormal Posistance Junation to Ambient (Note 6)  | Steady State           | П                                | 62          | °C/W  |  |
| Thermal Resistance, Junction to Ambient (Note 6) | t < 10s                | $R_{\theta JA}$                  | 43          |       |  |
| Thermal Resistance, Junction to Case (Note 6)    | Steady State           | $R_{\theta JC}$                  | 9.4         | °C/W  |  |
| Operating and Storage Temperature Range          |                        | T <sub>J,</sub> T <sub>STG</sub> | -55 to +150 | °C    |  |

### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic                             | Symbol              | Min | Тур  | Max  | Unit  | Test Condition                                |  |
|--|---------------------|-----|------|------|-------|---|--|
| OFF CHARACTERISTICS (Note 8)               |                     |     | -    |      |       |   |  |
| Drain-Source Breakdown Voltage             | $BV_{DSS}$          | 30  | _    | _    | V     | $V_{GS} = 0V, I_D = 250\mu A$                 |  |
| Zero Gate Voltage Drain Current            | IDSS                | _   | _    | 1    | μA    | $V_{DS} = 30V, V_{GS} = 0V$                   |  |
| Gate-Source Leakage                        | I <sub>GSS</sub>    | _   | _    | ±100 | nA    | $V_{GS} = \pm 20V, V_{DS} = 0V$               |  |
| ON CHARACTERISTICS (Note 8)                |                     |     |      |      |       |   |  |
| Gate Threshold Voltage                     | $V_{GS(TH)}$        | 1.0 | _    | 2.0  | V     | $V_{DS} = V_{GS}, I_{D} = 250 \mu A$          |  |
| Static Drain-Source On-Resistance          |                     | _   | _    | 20.5 | mΩ    | $V_{GS} = 10V, I_D = 7A$                      |  |
| Static Dialii-Source Off-Resistance        | R <sub>DS(ON)</sub> | _   | _    | 30   | 11122 | $V_{GS} = 4.5V, I_D = 7A$                     |  |
| Diode Forward Voltage                      | $V_{SD}$            | _   | 0.70 | 1.0  | V     | $V_{GS} = 0V, I_{S} = 1A$                     |  |
| DYNAMIC CHARACTERISTICS (Note 9)           |                     |     |      |      |       |   |  |
| Input Capacitance                          | C <sub>iss</sub>    |     | 641  | _    |       | 45)/ )/                                       |  |
| Output Capacitance                         | Coss                | _   | 66   | _    | pF    | $V_{DS} = 15V, V_{GS} = 0V,$<br>f = 1.0MHz    |  |
| Reverse Transfer Capacitance               | C <sub>rss</sub>    | _   | 50   | _    |       | 1 - 1.000112                                  |  |
| Gate Resistance                            | $R_g$               | _   | 2.2  | _    | Ω     | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$        |  |
| Total Gate Charge (V <sub>GS</sub> = 4.5V) | Qg                  | _   | 6    | _    |       |   |  |
| Total Gate Charge (V <sub>GS</sub> = 10V)  | Qg                  | _   | 13.2 | _    | nC    | \/ - 45\/   - 40A                             |  |
| Gate-Source Charge                         | $Q_{gs}$            |     | 1.7  | _    | IIC   | $V_{DS} = 15V, I_{D} = 10A$                   |  |
| Gate-Drain Charge                          | $Q_{gd}$            | _   | 2.2  | _    |       |   |  |
| Turn-On Delay Time                         | t <sub>D(ON)</sub>  | _   | 3.3  | _    |       |   |  |
| Turn-On Rise Time                          | $t_R$               | _   | 4.4  | _    |       | V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, |  |
| Turn-Off Delay Time                        | t <sub>D(OFF)</sub> |     | 22.3 | _    | ns    | $R_G = 6\Omega$ , $I_D = 1A$                  |  |
| Turn-Off Fall Time                         | $t_{F}$             |     | 5.3  | _    |       |   |  |
| Reverse Recovery Time                      | t <sub>RR</sub>     | _   | 11.4 | _    | ns    | I <sub>F</sub> = 11A, di/dt = 100A/μs         |  |
| Reverse Recovery Charge                    | Q <sub>RR</sub>     | _   | 8.2  | _    | nC    | I <sub>F</sub> = 11A, di/dt = 100A/µs         |  |

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

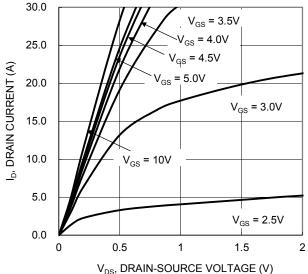
<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

<sup>7.</sup>  $I_{AS}$  and  $E_{AS}$  rating are based on low frequency and duty cycles to keep  $T_J$  = +25°C.

<sup>8.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>9.</sup> Guaranteed by design. Not subject to product testing.





V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic

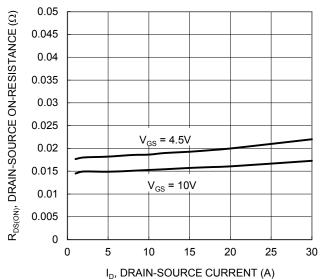


Figure 3. Typical On-Resistance vs Drain Current and Gate Voltage

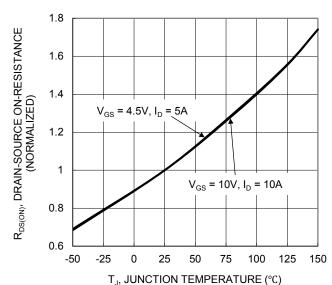


Figure 5. On-Resistance Variation with Temperature

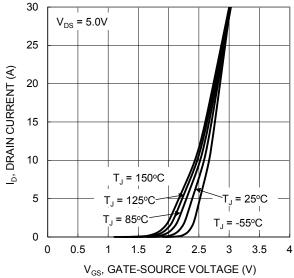


Figure 2. Typical Transfer Characteristic

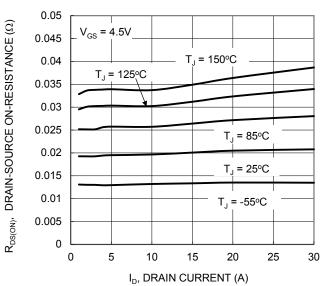


Figure 4. Typical On-Resistance vs Drain Current and Temperature

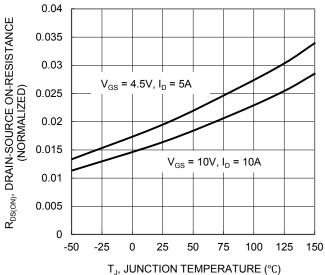


Figure 6.On-Resistance Variation with Temperature





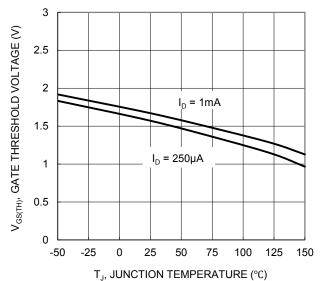
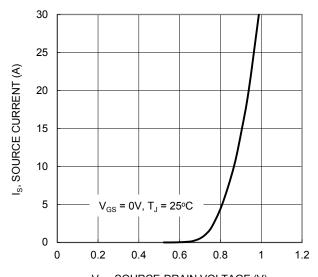


Figure 7. Gate Threshold Variation vs Junction
Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 8. Diode Forward Voltage vs. Current

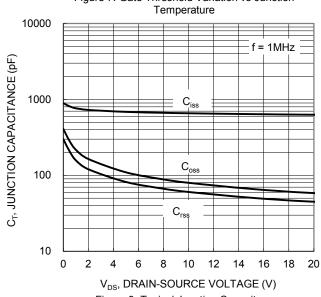


Figure 9. Typical Junction Capacitance

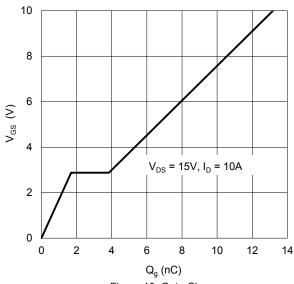


Figure 10. Gate Charge

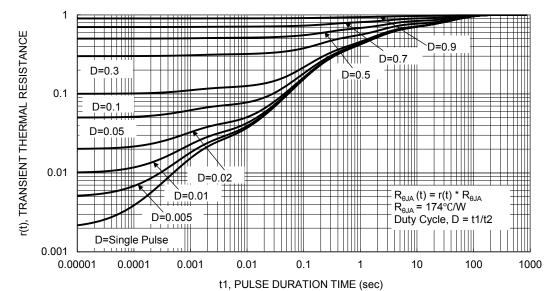


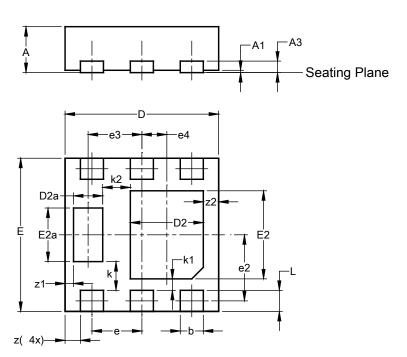
Figure 11. Transient Thermal Resistance



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### U-DFN2020-6 (Type F)

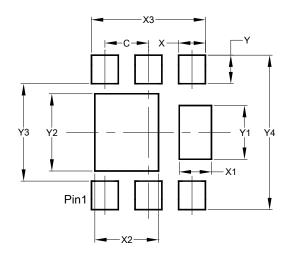


|       | U-DFN2020-6 |          |       |  |  |  |  |  |
|-------|-------------|----------|-------|--|--|--|--|--|
|       | (Type F)    |          |       |  |  |  |  |  |
| Dim   | Min         |          |       |  |  |  |  |  |
| Α     | 0.57        | 0.63     | 0.60  |  |  |  |  |  |
| A1    | 0.00        | 0.05     | 0.03  |  |  |  |  |  |
| A3    | -           | -        | 0.15  |  |  |  |  |  |
| b     | 0.25        | 0.35     | 0.30  |  |  |  |  |  |
| D     | 1.95        | 2.05     | 2.00  |  |  |  |  |  |
| D2    | 0.85        | 1.05     | 0.95  |  |  |  |  |  |
| D2a   | 0.33        | 0.43     | 0.38  |  |  |  |  |  |
| Е     | 1.95        | 2.05     | 2.00  |  |  |  |  |  |
| E2    | 1.05        | 1.25     | 1.15  |  |  |  |  |  |
| E2a   | 0.65        | 0.75     | 0.70  |  |  |  |  |  |
| е     |             | 0.65 BS  | _     |  |  |  |  |  |
| e2    |             | ).863 BS |       |  |  |  |  |  |
| е3    |             | 0.70 BS  | С     |  |  |  |  |  |
| e4    | C           | ).325 BS | SC SC |  |  |  |  |  |
| k     |             | 0.37 BS  | С     |  |  |  |  |  |
| k1    |             | 0.15 BS  | С     |  |  |  |  |  |
| k2    |             | 0.36 BS  | С     |  |  |  |  |  |
| L     |             | 0.325    |       |  |  |  |  |  |
| Z     | 0.20 BSC    |          |       |  |  |  |  |  |
| z1    | 0.110 BSC   |          |       |  |  |  |  |  |
| z2    |             | 0.20 BS  | _     |  |  |  |  |  |
| All C | imens       | ions in  | mm    |  |  |  |  |  |

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### U-DFN2020-6 (Type F)



| Dimensions | value   |
|------------|---------|
|            | (in mm) |
| С          | 0.650   |
| X          | 0.400   |
| X1         | 0.480   |
| X2         | 0.950   |
| Х3         | 1.700   |
| Y          | 0.425   |
| Y1         | 0.800   |
| Y2         | 1.150   |
| Y3         | 1.450   |
| Y4         | 2.300   |

Value



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